

SOT-323 Plastic-Encapsulate Transistors

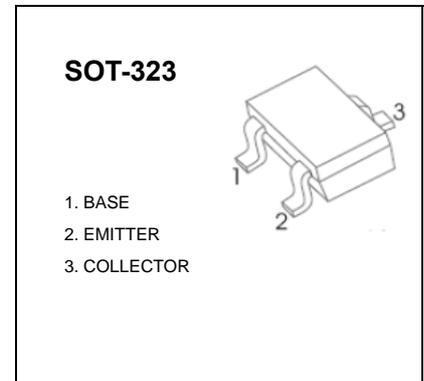
TRANSISTOR (PNP)

FEATURES

- Ideally suited for automatic insertion
- Epitaxial planar die construction
- Complementary to BC817W

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-500	mA
P_C	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	417	$^\circ\text{C}/\text{W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C=-10\mu\text{A}, I_E=0$	-50		V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=-10\text{mA}, I_B=0$	-45		V
Emitter-base breakdown voltage	V_{EBO}	$I_E=-1\mu\text{A}, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-20\text{V}, I_E=0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-20\text{V}, I_B=0$		-0.2	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1\text{V}, I_C=-100\text{mA}$	100	600	
	$h_{FE(2)}$	$V_{CE}=-1\text{V}, I_C=-500\text{mA}$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$		-0.7	V
Base-emitter voltage	$V_{BE(on)}$	$V_{CE}=-1\text{V}, I_C=-500\text{mA}$		-1.2	V
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$ $f=100\text{MHz}$	80		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, f=1\text{MHz}$		10	pF

CLASSIFICATION of $h_{FE(1)}$

Rank	BC807-16W	BC807-25W	BC807-40W
Range	100-250	160-400	250-600
Marking	5A	5B	5C

Typical Characteristics

